

# **PMV42ENER Datasheet**



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DiGi Electronics Part Number PMV42ENER-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PMV42ENER

Description MOSFET N-CH 30V 4.4A TO236AB

Detailed Description N-Channel 30 V 4.4A (Ta) 500mW (Ta), 5W (Tc) Surf

ace Mount TO-236AB



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# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
PMV42ENER	Nexperia USA Inc.
Series:	Product Status:
	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
30 V	4.4A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
4.5V, 10V	36mOhm @ 4.4A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
2V @ 250μA	9 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	281 pF @ 15 V
FET Feature:	Power Dissipation (Max):
	500mW (Ta), 5W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
TO-236AB	TO-236-3, SC-59, SOT-23-3
Base Product Number:	
PMV42	

# **Environmental & Export classification**

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



# PMV42ENE

# 30 V, N-channel Trench MOSFET

16 March 2016

Product data sheet

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Logic level compatible
- Low on-state resistance
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 1 kV HBM
- Enhanced power dissipation capability of 1 W

### 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
$V_{GS}$	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	-	5.1	Α
Static characteristics					•		
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 4.4 A; T <sub>j</sub> = 25 °C		-	29	36	mΩ

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



30 V, N-channel Trench MOSFET

# 5. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain	TO-236AB (SOT23)	G S 017aaa255

# 6. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PMV42ENE	TO-236AB	plastic surface-mounted package; 3 leads	SOT23	

# 7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV42ENE	BL%

[1] % = placeholder for manufacturing site code

30 V, N-channel Trench MOSFET

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	5.1	Α
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	4.4	Α
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	2.7	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	18	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	500	mW
			[1]	-	1.04	W
		T <sub>sp</sub> = 25 °C		-	5	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drai	n diode					,
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	1	Α

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

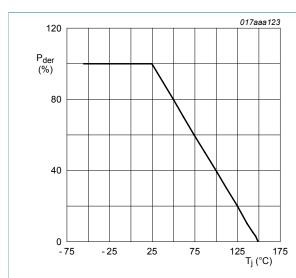


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

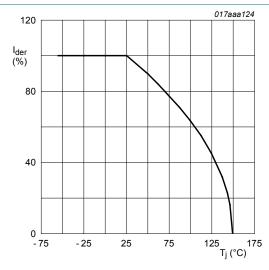


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

PMV42ENE

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#### 30 V, N-channel Trench MOSFET

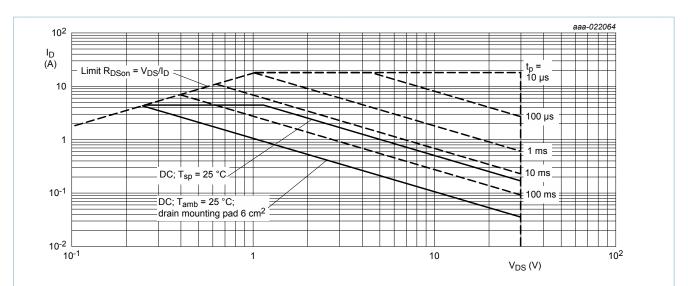


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

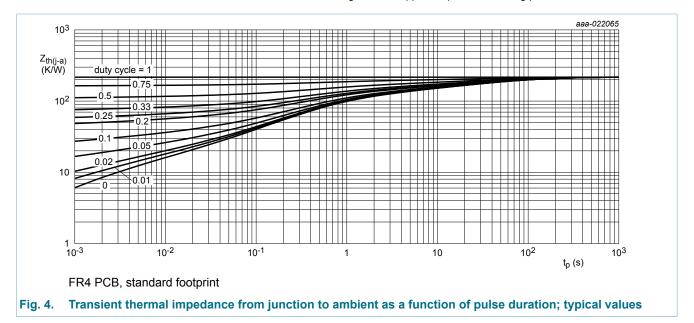
30 V, N-channel Trench MOSFET

#### 9. Thermal characteristics

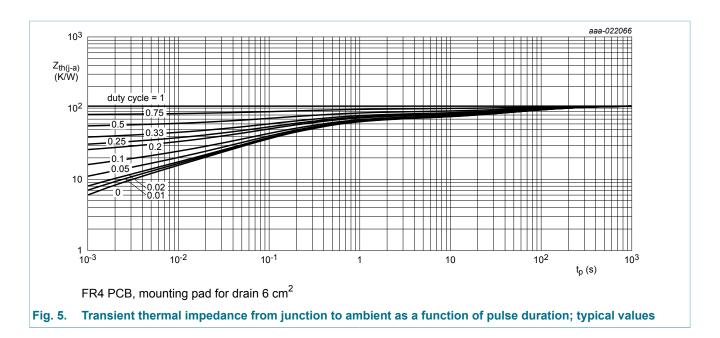
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		[1]	-	218	250	K/W
			[2]	-	105	120	K/W
		in free air; t ≤ 5 s	<u>[2]</u>	-	72	83	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	20	25	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



#### 30 V, N-channel Trench MOSFET



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## 10. Characteristics

#### Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1	1.4	2	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μΑ
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 4.4 A; T <sub>j</sub> = 25 °C	-	29	36	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 4.4 A; T <sub>j</sub> = 150 °C	-	46	57	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 3.5 A; T <sub>j</sub> = 25 °C	-	42	54	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 4.4 A; $T_{j}$ = 25 °C	-	7	-	S
$R_G$	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	-	1.5	-	Ω
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 4.4 A; V <sub>GS</sub> = 10 V;	-	5.5	9	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	8.0	-	nC
$Q_{GD}$	gate-drain charge		-	1.1	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	281	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	42	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	32	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 4.4 A; V <sub>GS</sub> = 10 V;	-	5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	18	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	9	-	ns
t <sub>f</sub>	fall time		-	3	-	ns
Source-dra	in diode		1	1	-	
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 1 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.8	1.2	V

#### 30 V, N-channel Trench MOSFET

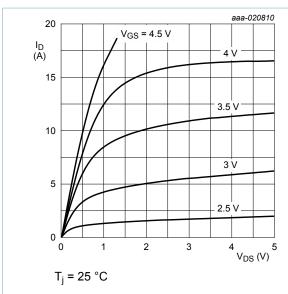


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

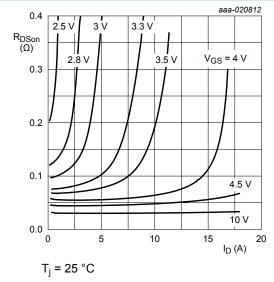


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

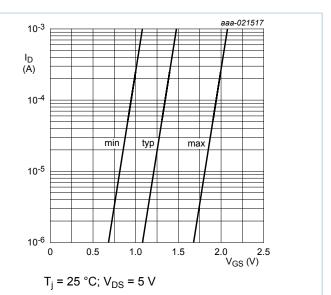


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

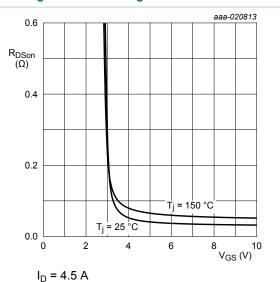


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

#### 30 V, N-channel Trench MOSFET

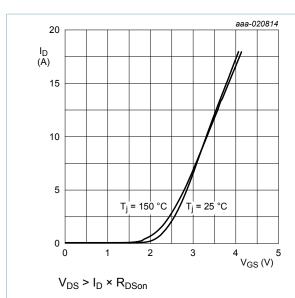


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

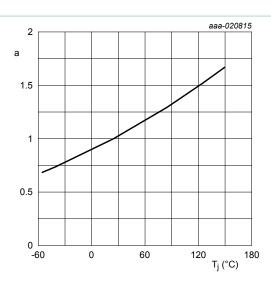


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

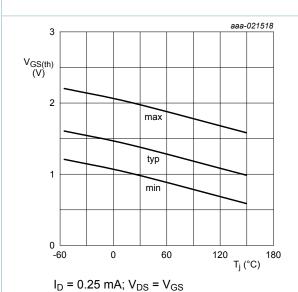
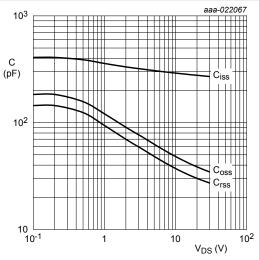


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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#### 30 V, N-channel Trench MOSFET

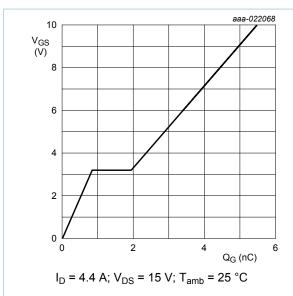


Fig. 14. Gate-source voltage as a function of gate charge; typical values

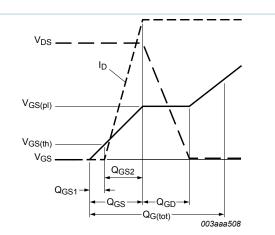


Fig. 15. MOSFET transistor: Gate charge waveform definitions

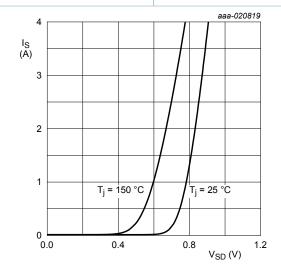
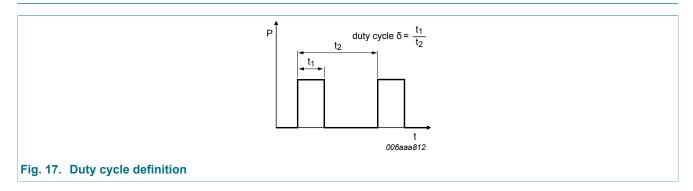


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$ 

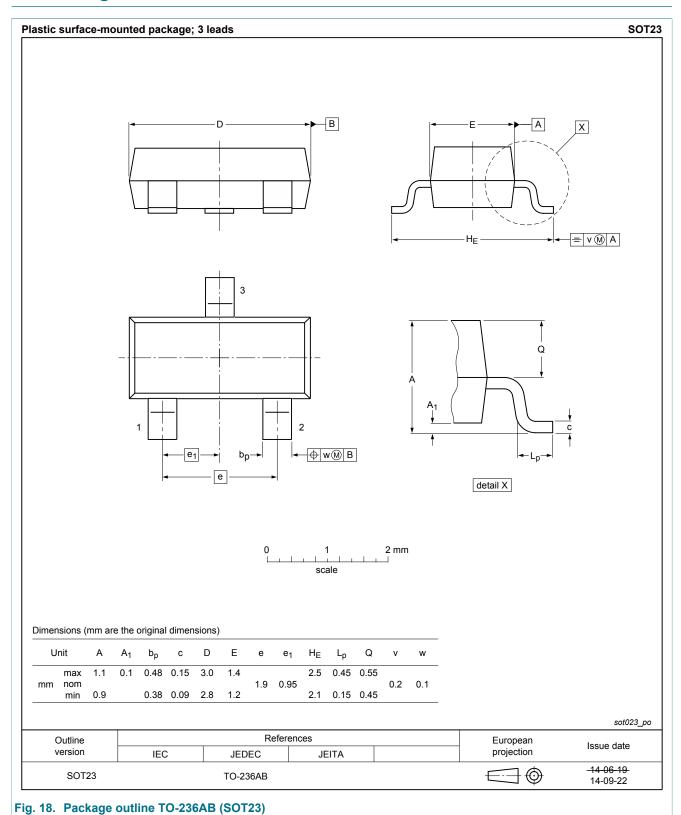
30 V, N-channel Trench MOSFET

# 11. Test information



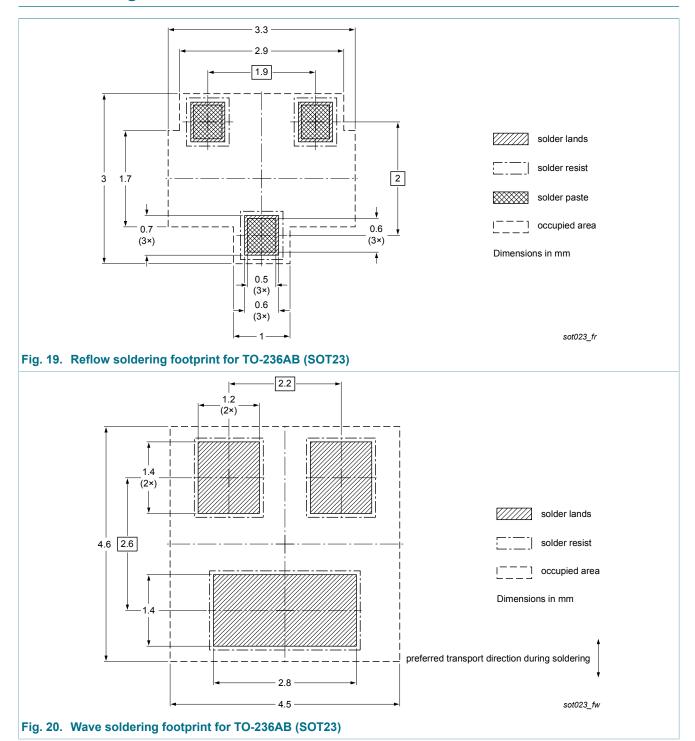
30 V, N-channel Trench MOSFET

# 12. Package outline



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## 13. Soldering



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# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV42ENE v.1	20160316	Product data sheet	-	-

#### 30 V, N-channel Trench MOSFET

### 15. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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